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Details	
Product Status	Obsolete
Number of LABs/CLBs	185000
Number of Logic Elements/Cells	490000
Total RAM Bits	41984000
Number of I/O	432
Number of Gates	-
Voltage - Supply	0.82V ~ 0.88V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	1517-FBGA (40x40)
Supplier Device Package	1517-FBGA (40x40)
Purchase URL	https://www.e-xfl.com/product-detail/intel/5sgxeb5r3f40i3l

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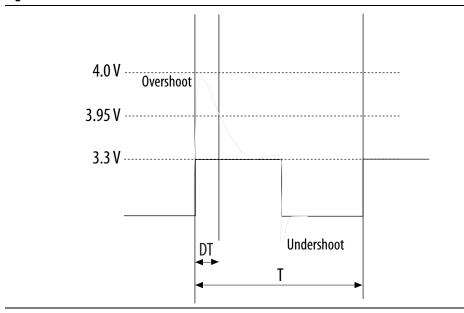
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Table 5 lists the maximum allowed input overshoot voltage and the duration of the overshoot voltage as a percentage of device lifetime. The maximum allowed overshoot duration is specified as a percentage of high time over the lifetime of the device. A DC signal is equivalent to 100% of the duty cycle. For example, a signal that overshoots to 3.95 V can be at 3.95 V for only ~21% over the lifetime of the device; for a device lifetime of 10 years, the overshoot duration amounts to ~2 years.

Table 5. Maximum Allowed Overshoot During Transitions

Symbol	Description	Condition (V)	Overshoot Duration as % @ T _J = 100°C	Unit
		3.8	100	%
		3.85	64	%
		3.9	36	%
		3.95	21	%
Vi (AC)	AC input voltage	4	12	%
		4.05	7	%
		4.1	4	%
		4.15	2	%
		4.2	1	%

Figure 1. Stratix V Device Overshoot Duration



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Recommended Operating Conditions

This section lists the functional operating limits for the AC and DC parameters for Stratix V devices. Table 6 lists the steady-state voltage and current values expected from Stratix V devices. Power supply ramps must all be strictly monotonic, without plateaus.

Table 6. Recommended Operating Conditions for Stratix V Devices (Part 1 of 2)

Symbol	Description	Condition	Min ⁽⁴⁾	Тур	Max ⁽⁴⁾	Unit
	Core voltage and periphery circuitry power supply (C1, C2, I2, and I3YY speed grades)	_	0.87	0.9	0.93	V
V _{CC}	Core voltage and periphery circuitry power supply (C2L, C3, C4, I2L, I3, I3L, and I4 speed grades) (3)	_	0.82	0.85	0.88	V
V _{CCPT}	Power supply for programmable power technology	_	1.45	1.50	1.55	V
V _{CC_AUX}	Auxiliary supply for the programmable power technology	_	2.375	2.5	2.625	V
V (1)	I/O pre-driver (3.0 V) power supply		2.85	3.0	3.15	V
V _{CCPD} ⁽¹⁾	I/O pre-driver (2.5 V) power supply		2.375	2.5	2.625	V
	I/O buffers (3.0 V) power supply	_	2.85	3.0	3.15	٧
	I/O buffers (2.5 V) power supply	_	2.375	2.5	2.625	V
	I/O buffers (1.8 V) power supply	_	1.71	1.8	1.89	٧
V_{CCIO}	I/O buffers (1.5 V) power supply	_	1.425	1.5	1.575	V
	I/O buffers (1.35 V) power supply		1.283	1.35	1.45	V
	I/O buffers (1.25 V) power supply		1.19	1.25	1.31	V
	I/O buffers (1.2 V) power supply	_	1.14	1.2	1.26	V
	Configuration pins (3.0 V) power supply		2.85	3.0	3.15	V
V_{CCPGM}	Configuration pins (2.5 V) power supply	_	2.375	2.5	2.625	V
	Configuration pins (1.8 V) power supply	_	1.71	1.8	1.89	V
V _{CCA_FPLL}	PLL analog voltage regulator power supply		2.375	2.5	2.625	V
V _{CCD_FPLL}	PLL digital voltage regulator power supply		1.45	1.5	1.55	V
V _{CCBAT} (2)	Battery back-up power supply (For design security volatile key register)	_	1.2	_	3.0	V
V _I	DC input voltage	_	-0.5	_	3.6	V
V ₀	Output voltage	_	0	_	V _{CCIO}	V
т.	Operating junction temperature	Commercial	0	_	85	°C
T _J	Operating junction temperature	Industrial	-40	_	100	°C

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Table 11. OCT Calibration Accuracy Specifications for Stratix V Devices (1) (Part 2 of 2)

			Calibration Accuracy					
Symbol	Description	Conditions	C1	C2,I2	C3,I3, I3YY	C4,I4	Unit	
50-Ω R _S	Internal series termination with calibration (50- Ω setting)	V _{CCIO} = 3.0, 2.5, 1.8, 1.5, 1.2 V	±15	±15	±15	±15	%	
$34\text{-}\Omega$ and $40\text{-}\Omega$ R_S	Internal series termination with calibration (34- Ω and 40- Ω setting)	V _{CCIO} = 1.5, 1.35, 1.25, 1.2 V	±15	±15	±15	±15	%	
48 - Ω , 60 - Ω , 80 - Ω , and 240 - Ω R _S	Internal series termination with calibration (48- Ω , 60- Ω , 80- Ω , and 240- Ω setting)	V _{CCIO} = 1.2 V	±15	±15	±15	±15	%	
50-Ω R _T	Internal parallel termination with calibration (50-Ω setting)	V _{CCIO} = 2.5, 1.8, 1.5, 1.2 V	-10 to +40	-10 to +40	-10 to +40	-10 to +40	%	
$\begin{array}{c} 20\text{-}\Omega,30\text{-}\Omega,\\ 40\text{-}\Omega,60\text{-}\Omega,\\ \text{and}\\ 120\text{-}\OmegaR_T \end{array}$	Internal parallel termination with calibration (20- Ω , 30- Ω , 40- Ω , 60- Ω , and 120- Ω setting)	V _{CCIO} = 1.5, 1.35, 1.25 V	-10 to +40	-10 to +40	-10 to +40	-10 to +40	%	
60- Ω and 120- Ω R _T	Internal parallel termination with calibration (60- Ω and 120- Ω setting)	V _{CCIO} = 1.2	-10 to +40	-10 to +40	-10 to +40	-10 to +40	%	
$\begin{array}{c} \textbf{25-}\Omega \\ \textbf{R}_{S_left_shift} \end{array}$	Internal left shift series termination with calibration (25- Ω R _{S_left_shift} setting)	V _{CCIO} = 3.0, 2.5, 1.8, 1.5, 1.2 V	±15	±15	±15	±15	%	

Note to Table 11:

Table 12 lists the Stratix V OCT without calibration resistance tolerance to PVT changes.

Table 12. OCT Without Calibration Resistance Tolerance Specifications for Stratix V Devices (Part 1 of 2)

			Resistance Tolerance				
Symbol	Description	Conditions	C1	C2,I2	C3, I3, I3YY	C4, I4	Unit
25-Ω R, 50-Ω R _S	Internal series termination without calibration (25- Ω setting)	V _{CCIO} = 3.0 and 2.5 V	±30	±30	±40	±40	%
25-Ω R _S	Internal series termination without calibration (25- Ω setting)	V _{CCIO} = 1.8 and 1.5 V	±30	±30	±40	±40	%
25-Ω R _S	Internal series termination without calibration (25- Ω setting)	V _{CCIO} = 1.2 V	±35	±35	±50	±50	%

⁽¹⁾ OCT calibration accuracy is valid at the time of calibration only.

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			Re	esistance	Tolerance	,	
Symbol	Description	Conditions	C1	C2,I2	C3, I3, I3YY	C4, I4	Unit
50-Ω R _S	Internal series termination without calibration (50- Ω setting)	V _{CCIO} = 1.8 and 1.5 V	±30	±30	±40	±40	%
50-Ω R _S	Internal series termination without calibration (50- Ω setting)	V _{CCIO} = 1.2 V	±35	±35	±50	±50	%
100-Ω R _D	Internal differential termination (100-Ω setting)	V _{CCPD} = 2.5 V	±25	±25	±25	±25	%

Calibration accuracy for the calibrated series and parallel OCTs are applicable at the moment of calibration. When voltage and temperature conditions change after calibration, the tolerance may change.

OCT calibration is automatically performed at power-up for OCT-enabled I/Os. Table 13 lists the OCT variation with temperature and voltage after power-up calibration. Use Table 13 to determine the OCT variation after power-up calibration and Equation 1 to determine the OCT variation without recalibration.

Equation 1. OCT Variation Without Recalibration for Stratix V Devices (1), (2), (3), (4), (5), (6)

$$R_{OCT} = R_{SCAL} \Big(1 + \langle \frac{dR}{dT} \times \Delta T \rangle \pm \langle \frac{dR}{dV} \times \Delta V \rangle \Big)$$

Notes to Equation 1:

- (1) The R_{OCT} value shows the range of OCT resistance with the variation of temperature and V_{CCIO} .
- (2) R_{SCAL} is the OCT resistance value at power-up.
- (3) ΔT is the variation of temperature with respect to the temperature at power-up.
- (4) ΔV is the variation of voltage with respect to the V_{CCIO} at power-up.
- (5) dR/dT is the percentage change of R_{SCAL} with temperature.
- (6) dR/dV is the percentage change of R_{SCAL} with voltage.

Table 13 lists the on-chip termination variation after power-up calibration.

Table 13. OCT Variation after Power-Up Calibration for Stratix V Devices (Part 1 of 2) (1)

Symbol	Description	V _{CCIO} (V)	Typical	Unit
		3.0	0.0297	
	007	2.5	0.0344	
dR/dV	OCT variation with voltage without recalibration	1.8	0.0499	%/mV
	Todanstation	1.5	0.0744	
		1.2	0.1241	

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Internal Weak Pull-Up Resistor

Table 16 lists the weak pull-up resistor values for Stratix V devices.

Table 16. Internal Weak Pull-Up Resistor for Stratix V Devices (1), (2)

Symbol	Description	V _{CC10} Conditions (V) ⁽³⁾	Value ⁽⁴⁾	Unit	
		3.0 ±5%	25	kΩ	
		2.5 ±5% 25			
	Value of the I/O pin pull-up resistor before	1.8 ±5%	25	kΩ	
R _{PU}	and during configuration, as well as user mode if you enable the programmable	1.5 ±5%	25	kΩ	
	pull-up resistor option.	1.35 ±5%	25	kΩ	
		1.25 ±5% 25		kΩ	
		1.2 ±5%	25	kΩ	

Notes to Table 16:

- (1) All I/O pins have an option to enable the weak pull-up resistor except the configuration, test, and JTAG pins.
- (2) The internal weak pull-down feature is only available for the JTAG TCK pin. The typical value for this internal weak pull-down resistor is approximately 25 k Ω .
- (3) The pin pull-up resistance values may be lower if an external source drives the pin higher than V_{CCIO} .
- (4) These specifications are valid with a ±10% tolerance to cover changes over PVT.

I/O Standard Specifications

Table 17 through Table 22 list the input voltage (V_{IH} and V_{IL}), output voltage (V_{OH} and V_{OL}), and current drive characteristics (I_{OH} and I_{OL}) for various I/O standards supported by Stratix V devices. These tables also show the Stratix V device family I/O standard specifications. The V_{OL} and V_{OH} values are valid at the corresponding I_{OH} and I_{OL} , respectively.

For an explanation of the terms used in Table 17 through Table 22, refer to "Glossary" on page 65. For tolerance calculations across all SSTL and HSTL I/O standards, refer to Altera knowledge base solution rd07262012_486.

Table 17. Single-Ended I/O Standards for Stratix V Devices

1/0	1/0			VII	_(V)	V _{IH}	(V)	V _{OL} (V)	V _{OH} (V)	I _{OL}	I _{OH}
Standard	Min	Тур	Max	Min	Max	Min	Max	Max	Min	(mĀ)	(mA)
LVTTL	2.85	3	3.15	-0.3	0.8	1.7	3.6	0.4	2.4	2	-2
LVCMOS	2.85	3	3.15	-0.3	0.8	1.7	3.6	0.2	V _{CCIO} - 0.2	0.1	-0.1
2.5 V	2.375	2.5	2.625	-0.3	0.7	1.7	3.6	0.4	2	1	-1
1.8 V	1.71	1.8	1.89	-0.3	0.35 * V _{CCIO}	0.65 * V _{CCIO}	V _{CCIO} + 0.3	0.45	V _{CCIO} – 0.45	2	-2
1.5 V	1.425	1.5	1.575	-0.3	0.35 * V _{CCIO}	0.65 * V _{CCIO}	V _{CCIO} + 0.3	0.25 * V _{CCIO}	0.75 * V _{CCIO}	2	-2
1.2 V	1.14	1.2	1.26	-0.3	0.35 * V _{CCIO}	0.65 * V _{CCIO}	V _{CCIO} + 0.3	0.25 * V _{CCIO}	0.75 * V _{CCIO}	2	-2

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Table 18. Single-Ended SSTL, HSTL, and HSUL I/O Reference Voltage Specifications for Stratix V Devices

I/O Standard		V _{CCIO} (V)			V _{REF} (V)			V _{ττ} (V)			
I/O Standard	Min	Тур	Max	Min	Тур	Max	Min	Тур	Мах		
SSTL-2 Class I, II	2.375	2.5	2.625	0.49 * V _{CCIO}	0.5 * V _{CCIO}	0.51 * V _{CCIO}	V _{REF} – 0.04	V_{REF}	V _{REF} + 0.04		
SSTL-18 Class I, II	1.71	1.8	1.89	0.833	0.9	0.969	V _{REF} – 0.04	V _{REF}	V _{REF} + 0.04		
SSTL-15 Class I, II	1.425	1.5	1.575	0.49 * V _{CCIO}	0.5 * V _{CCIO}	0.51 * V _{CCIO}	0.49 * V _{CCIO}	0.5 * VCCIO	0.51 * V _{CCIO}		
SSTL-135 Class I, II	1.283	1.35	1.418	0.49 * V _{CCIO}	0.5 * V _{CCIO}	0.51 * V _{CCIO}	0.49 * V _{CCIO}	0.5 * V _{CCIO}	0.51 * V _{CCIO}		
SSTL-125 Class I, II	1.19	1.25	1.26	0.49 * V _{CCIO}	0.5 * V _{CCIO}	0.51 * V _{CCIO}	0.49 * V _{CCIO}	0.5 * VCCIO	0.51 * V _{CCIO}		
SSTL-12 Class I, II	1.14	1.20	1.26	0.49 * V _{CCIO}	0.5 * V _{CCIO}	0.51 * V _{CCIO}	0.49 * V _{CCIO}	0.5 * VCCIO	0.51 * V _{CCIO}		
HSTL-18 Class I, II	1.71	1.8	1.89	0.85	0.9	0.95	_	V _{CCIO} /2	_		
HSTL-15 Class I, II	1.425	1.5	1.575	0.68	0.75	0.9	_	V _{CCIO} /2	_		
HSTL-12 Class I, II	1.14	1.2	1.26	0.47 * V _{CCIO}	0.5 * V _{CCIO}	0.53 * V _{CCIO}	_	V _{CCIO} /2	_		
HSUL-12	1.14	1.2	1.3	0.49 * V _{CCIO}	0.5 * V _{CCIO}	0.51 * V _{CCIO}	_	_	_		

Table 19. Single-Ended SSTL, HSTL, and HSUL I/O Standards Signal Specifications for Stratix V Devices (Part 1 of 2)

I/O Standard	V _{IL(D(}	; ₎ (V)	V _{IH(D}	_{C)} (V)	V _{IL(AC)} (V)	V _{IH(AC)} (V)	V _{OL} (V)	V _{OH} (V)	I (mA)	l _{oh}
i/U Stanuaru	Min	Max	Min	Max	Max	Min	Max	Min	I _{ol} (mA)	(mA)
SSTL-2 Class I	-0.3	V _{REF} – 0.15	V _{REF} + 0.15	V _{CCIO} + 0.3	V _{REF} – 0.31	V _{REF} + 0.31	V _{TT} – 0.608	V _{TT} + 0.608	8.1	-8.1
SSTL-2 Class II	-0.3	V _{REF} – 0.15	V _{REF} + 0.15	V _{CCIO} + 0.3	V _{REF} – 0.31	V _{REF} + 0.31	V _{TT} – 0.81	V _{TT} + 0.81	16.2	-16.2
SSTL-18 Class I	-0.3	V _{REF} – 0.125	V _{REF} + 0.125	V _{CCIO} + 0.3	V _{REF} – 0.25	V _{REF} + 0.25	V _{TT} – 0.603	V _{TT} + 0.603	6.7	-6.7
SSTL-18 Class II	-0.3	V _{REF} – 0.125	V _{REF} + 0.125	V _{CCIO} + 0.3	V _{REF} – 0.25	V _{REF} + 0.25	0.28	V _{CCIO} - 0.28	13.4	-13.4
SSTL-15 Class I	_	V _{REF} – 0.1	V _{REF} + 0.1	_	V _{REF} – 0.175	V _{REF} + 0.175	0.2 * V _{CCIO}	0.8 * V _{CCIO}	8	-8
SSTL-15 Class II	_	V _{REF} – 0.1	V _{REF} + 0.1	_	V _{REF} – 0.175	V _{REF} + 0.175	0.2 * V _{CCIO}	0.8 * V _{CCIO}	16	-16
SSTL-135 Class I, II	_	V _{REF} – 0.09	V _{REF} + 0.09	_	V _{REF} – 0.16	V _{REF} + 0.16	0.2 * V _{CCIO}	0.8 * V _{CCIO}	_	_
SSTL-125 Class I, II	_	V _{REF} – 0.85	V _{REF} + 0.85	_	V _{REF} – 0.15	V _{REF} + 0.15	0.2 * V _{CCIO}	0.8 * V _{CCIO}	_	_
SSTL-12 Class I, II	_	V _{REF} – 0.1	V _{REF} + 0.1	_	V _{REF} – 0.15	V _{REF} + 0.15	0.2 * V _{CCIO}	0.8 * V _{CCIO}	_	_

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Table 21. Differential HSTL and HSUL I/O Standards for Stratix V Devices (Part 2 of 2)

I/O V _{CCIO} (V)		V _{DIF(DC)} (V)		V _{X(AC)} (V)				V _{CM(DC)} (V)	V _{DIF(AC)} (V)			
Standard	Min	Тур	Max	Min	Max	Min	Тур	Max	Min	Тур	Max	Min	Max
HSTL-12 Class I, II	1.14	1.2	1.26	0.16	V _{CCIO} + 0.3	_	0.5* V _{CCIO}	_	0.4* V _{CCIO}	0.5* V _{CCIO}	0.6* V _{CCIO}	0.3	V _{CCIO} + 0.48
HSUL-12	1.14	1.2	1.3	0.26	0.26	0.5*V _{CCIO} - 0.12	0.5* V _{CCIO}	0.5*V _{CCIO} + 0.12	0.4* V _{CCIO}	0.5* V _{CCIO}	0.6* V _{CCIO}	0.44	0.44

Table 22. Differential I/O Standard Specifications for Stratix V Devices (7)

I/O	V _{CCIO} (V) ⁽¹⁰⁾			V _{ID} (mV) ⁽⁸⁾				$V_{ICM(DC)}$ (V)		V _{OD} (V) ⁽⁶⁾			V _{OCM} (V) ⁽⁶⁾		
Standard	Min	Тур	Max	Min	Condition	Max	Min	Condition	Max	Min	Тур	Max	Min	Тур	Max
PCML	Trar	nsmitte						of the high-s I/O pin speci							. For
2.5 V	2.375	2.5	2.625	100	V _{CM} =	_	0.05	D _{MAX} ≤ 700 Mbps	1.8	0.247	_	0.6	1.125	1.25	1.375
LVDS (1)	2.373	2.3	2.023	100	1.25 V		1.05	D _{MAX} > 700 Mbps	1.55	0.247	_	0.6	1.125	1.25	1.375
BLVDS (5)	2.375	2.5	2.625	100	_	_	_	_	_	_	_	_	_	_	_
RSDS (HIO) ⁽²⁾	2.375	2.5	2.625	100	V _{CM} = 1.25 V	_	0.3	_	1.4	0.1	0.2	0.6	0.5	1.2	1.4
Mini- LVDS (HIO) (3)	2.375	2.5	2.625	200	_	600	0.4	_	1.325	0.25	_	0.6	1	1.2	1.4
LVPECL (4	_	_	_	300	_	_	0.6	D _{MAX} ≤ 700 Mbps	1.8	_	_	_	_	_	
), (9)	_	_	_	300	_	_	1	D _{MAX} > 700 Mbps	1.6	_	_	_	_	_	_

Notes to Table 22:

- (1) For optimized LVDS receiver performance, the receiver voltage input range must be between 1.0 V to 1.6 V for data rates above 700 Mbps, and 0 V to 1.85 V for data rates below 700 Mbps.
- (2) For optimized RSDS receiver performance, the receiver voltage input range must be between 0.25 V to 1.45 V.
- (3) For optimized Mini-LVDS receiver performance, the receiver voltage input range must be between 0.3 V to 1.425 V.
- (4) For optimized LVPECL receiver performance, the receiver voltage input range must be between 0.85 V to 1.75 V for data rate above 700 Mbps and 0.45 V to 1.95 V for data rate below 700 Mbps.
- (5) There are no fixed V_{ICM} , V_{OD} , and V_{OCM} specifications for BLVDS. They depend on the system topology.
- (6) RL range: $90 \le RL \le 110 \Omega$.
- (7) The 1.4-V and 1.5-V PCML transceiver I/O standard specifications are described in "Transceiver Performance Specifications" on page 18.
- (8) The minimum VID value is applicable over the entire common mode range, VCM.
- (9) LVPECL is only supported on dedicated clock input pins.
- (10) Differential inputs are powered by VCCPD which requires 2.5 $\rm V.$

Power Consumption

Altera offers two ways to estimate power consumption for a design—the Excel-based Early Power Estimator and the Quartus[®] II PowerPlay Power Analyzer feature.

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Table 28. Transceiver Specifications for Stratix V GT Devices (Part 3 of 5) $^{(1)}$

Symbol/	Conditions		Transceiver Speed Grade			Transceive peed Grade		Unit
Description		Min	Тур	Max	Min	Тур	Max	
Differential on-chip termination resistors (7)	GT channels	_	100	_	_	100	_	Ω
	85-Ω setting	_	85 ± 30%	_	_	85 ± 30%	_	Ω
Differential on-chip termination resistors	100-Ω setting	_	100 ± 30%	_	_	100 ± 30%	_	Ω
for GX channels (19)	120-Ω setting	_	120 ± 30%	_	_	120 ± 30%	_	Ω
	150-Ω setting	_	150 ± 30%	_	_	150 ± 30%	_	Ω
V _{ICM} (AC coupled)	GT channels	_	650	_	_	650	_	mV
	VCCR_GXB = 0.85 V or 0.9 V	_	600	_	_	600	_	mV
VICM (AC and DC coupled) for GX Channels	VCCR_GXB = 1.0 V full bandwidth	_	700	_	_	700	_	mV
	VCCR_GXB = 1.0 V half bandwidth	_	750	_	_	750	_	mV
t _{LTR} ⁽⁹⁾	_	_	_	10	_	_	10	μs
t _{LTD} ⁽¹⁰⁾	_	4	_	_	4	_	_	μs
t _{LTD_manual} (11)		4	_	_	4	_	_	μs
t _{LTR_LTD_manual} (12)		15	_	_	15	_	_	μs
Run Length	GT channels	_	_	72	_	_	72	CID
nuii Leiigiii	GX channels				(8)			
CDR PPM	GT channels	_	_	1000	_	_	1000	± PPM
ODITITIVI	GX channels				(8)			
Programmable	GT channels	_	_	14	_	_	14	dB
equalization (AC Gain) ⁽⁵⁾	GX channels				(8)			
Programmable	GT channels	_	_	7.5	_	_	7.5	dB
DC gain ⁽⁶⁾	GX channels				(8)			
Differential on-chip termination resistors ⁽⁷⁾	GT channels		100	_	_	100	_	Ω
Transmitter	· '		•			•	•	
Supported I/O Standards	_			1.4-V	and 1.5-V F	PCML		
Data rate (Standard PCS)	GX channels	600	_	8500	600	_	8500	Mbps
Data rate (10G PCS)	GX channels	600	_	12,500	600		12,500	Mbps

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PLL Specifications

Table 31 lists the Stratix V PLL specifications when operating in both the commercial junction temperature range (0° to 85°C) and the industrial junction temperature range (-40° to 100° C).

Table 31. PLL Specifications for Stratix V Devices (Part 1 of 3)

Symbol	Parameter	Min	Тур	Max	Unit
	Input clock frequency (C1, C2, C2L, I2, and I2L speed grades)	5	_	800 (1)	MHz
f _{IN}	Input clock frequency (C3, I3, I3L, and I3YY speed grades)	5	_	800 (1)	MHz
	Input clock frequency (C4, I4 speed grades)	5	_	650 ⁽¹⁾	MHz
f _{INPFD}	Input frequency to the PFD	5	_	325	MHz
FINPFD	Fractional Input clock frequency to the PFD	50	_	160	MHz
	PLL VCO operating range (C1, C2, C2L, I2, I2L speed grades)	600	_	1600	MHz
f _{vco} ⁽⁹⁾	PLL VCO operating range (C3, I3, I3L, I3YY speed grades)	600	_	1600	MHz
	PLL VCO operating range (C4, I4 speed grades)	600	_	1300	MHz
EINDUTY	Input clock or external feedback clock input duty cycle	40	_	60	%
	Output frequency for an internal global or regional clock (C1, C2, C2L, I2, I2L speed grades)	_	_	717 (2)	MHz
Гоит	Output frequency for an internal global or regional clock (C3, I3, I3L speed grades)	_	_	650 ⁽²⁾	MHz
	Output frequency for an internal global or regional clock (C4, I4 speed grades)	_	_	580 ⁽²⁾	MHz
	Output frequency for an external clock output (C1, C2, C2L, I2, I2L speed grades)	_	_	800 (2)	MHz
f _{OUT_EXT}	Output frequency for an external clock output (C3, I3, I3L speed grades)	_	_	667 (2)	MHz
	Output frequency for an external clock output (C4, I4 speed grades)	_	_	553 ⁽²⁾	MHz
t _{оитриту}	Duty cycle for a dedicated external clock output (when set to 50%)	45	50	55	%
FCOMP	External feedback clock compensation time	_	_	10	ns
DYCONFIGCLK	Dynamic Configuration Clock used for mgmt_clk and scanclk	_	_	100	MHz
Lock	Time required to lock from the end-of-device configuration or deassertion of areset	_	_	1	ms
DLOCK	Time required to lock dynamically (after switchover or reconfiguring any non-post-scale counters/delays)	_	_	1	ms
	PLL closed-loop low bandwidth		0.3		MHz
: CLBW	PLL closed-loop medium bandwidth		1.5		MHz
	PLL closed-loop high bandwidth (7)	_	4	_	MHz
PLL_PSERR	Accuracy of PLL phase shift		_	±50	ps
ARESET	Minimum pulse width on the areset signal	10	_	_	ns

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Periphery Performance

This section describes periphery performance, including high-speed I/O and external memory interface.

I/O performance supports several system interfaces, such as the **LVDS** high-speed I/O interface, external memory interface, and the **PCI/PCI-X** bus interface. General-purpose I/O standards such as 3.3-, 2.5-, 1.8-, and 1.5-**LVTTL/LVCMOS** are capable of a typical 167 MHz and 1.2-**LVCMOS** at 100 MHz interfacing frequency with a 10 pF load.



The actual achievable frequency depends on design- and system-specific factors. Ensure proper timing closure in your design and perform HSPICE/IBIS simulations based on your specific design and system setup to determine the maximum achievable frequency in your system.

High-Speed I/O Specification

Table 36 lists high-speed I/O timing for Stratix V devices.

Table 36. High-Speed I/O Specifications for Stratix V Devices (1), (2) (Part 1 of 4)

_														
Cumbal	Conditions		C1		C2,	C2L, I	2, I2L	C3,	13, I3L	., I3YY		C4,I	4	Unit
Symbol	Conuntions	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f _{HSCLK_in} (input clock frequency) True Differential I/O Standards	Clock boost factor W = 1 to 40 (4)	5		800	5	_	800	5		625	5		525	MHz
f _{HSCLK_in} (input clock frequency) Single Ended I/O Standards (3)	Clock boost factor W = 1 to 40 (4)	5		800	5	_	800	5		625	5		525	MHz
f _{HSCLK_in} (input clock frequency) Single Ended I/O Standards	Clock boost factor W = 1 to 40 (4)	5		520	5	_	520	5		420	5		420	MHz
f _{HSCLK_OUT} (output clock frequency)	_	5		800	5	_	800	5		625 (5)	5		525 (5)	MHz

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Table 36. High-Speed I/O Specifications for Stratix V Devices (1), (2) (Part 4 of 4)

Cumbal	Symbol Conditions		C1		C2,	C2L, I	2, I2L	C3,	I3, I3I	., I3YY		C4,I4	4	II-ni4
Symbol	Contactions	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
	SERDES factor J = 3 to 10	(6)	_	(8)	(6)	_	(8)	(6)	_	(8)	(6)	_	(8)	Mbps
f _{HSDR} (data rate)	SERDES factor J = 2, uses DDR Registers	(6)		(7)	(6)	_	(7)	(6)	_	(7)	(6)		(7)	Mbps
	SERDES factor J = 1, uses SDR Register	(6)	_	(7)	(6)	_	(7)	(6)	_	(7)	(6)		(7)	Mbps
DPA Mode														
DPA run length	_	_	_	1000 0	_		1000 0	_	_	1000 0	_	_	1000 0	UI
Soft CDR mod	e													
Soft-CDR PPM tolerance	_	_	_	300	_	_	300	_	_	300	_	_	300	± PPM
Non DPA Mode	е													
Sampling Window	_	_		300			300	_		300	_		300	ps

Notes to Table 36:

- (1) When J = 3 to 10, use the serializer/deserializer (SERDES) block.
- (2) When J = 1 or 2, bypass the SERDES block.
- (3) This only applies to DPA and soft-CDR modes.
- (4) Clock Boost Factor (W) is the ratio between the input data rate to the input clock rate.
- (5) This is achieved by using the **LVDS** clock network.
- (6) The minimum specification depends on the clock source (for example, the PLL and clock pin) and the clock routing resource (global, regional, or local) that you use. The I/O differential buffer and input register do not have a minimum toggle rate.
- (7) The maximum ideal frequency is the SERDES factor (J) x the PLL maximum output frequency (fOUT) provided you can close the design timing and the signal integrity simulation is clean.
- (8) You can estimate the achievable maximum data rate for non-DPA mode by performing link timing closure analysis. You must consider the board skew margin, transmitter delay margin, and receiver sampling margin to determine the maximum data rate supported.
- (9) If the receiver with DPA enabled and transmitter are using shared PLLs, the minimum data rate is 150 Mbps.
- (10) You must calculate the leftover timing margin in the receiver by performing link timing closure analysis. You must consider the board skew margin, transmitter channel-to-channel skew, and receiver sampling margin to determine leftover timing margin.
- (11) The F_{MAX} specification is based on the fast clock used for serial data. The interface F_{MAX} is also dependent on the parallel clock domain which is design-dependent and requires timing analysis.
- (12) Stratix V RX LVDS will need DPA. For Stratix V TX LVDS, the receiver side component must have DPA.
- (13) Stratix V LVDS serialization and de-serialization factor needs to be x4 and above.
- (14) Requires package skew compensation with PCB trace length.
- (15) Do not mix single-ended I/O buffer within LVDS I/O bank.
- (16) Chip-to-chip communication only with a maximum load of 5 pF.
- (17) When using True LVDS RX channels for emulated LVDS TX channel, only serialization factors 1 and 2 are supported.

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Table 40. DQS Phase Offset Delay Per Setting for Stratix V Devices (1), (2) (Part 2 of 2)

Speed Grade	Min	Max	Unit
C4,I4	8	16	ps

Notes to Table 40:

- (1) The typical value equals the average of the minimum and maximum values.
- (2) The delay settings are linear with a cumulative delay variation of 40 ps for all speed grades. For example, when using a -2 speed grade and applying a 10-phase offset setting to a 90° phase shift at 400 MHz, the expected average cumulative delay is [625 ps + (10 × 10 ps) ± 20 ps] = 725 ps ± 20 ps.

Table 41 lists the DQS phase shift error for Stratix V devices.

Table 41. DQS Phase Shift Error Specification for DLL-Delayed Clock (t_{DQS_PSERR}) for Stratix V Devices (1)

Number of DQS Delay Buffers	C1	C2, C2L, I2, I2L	C3, I3, I3L, I3YY	C4,I4	Unit
1	28	28	30	32	ps
2	56	56	60	64	ps
3	84	84	90	96	ps
4	112	112	120	128	ps

Notes to Table 41:

Table 42 lists the memory output clock jitter specifications for Stratix V devices.

Table 42. Memory Output Clock Jitter Specification for Stratix V Devices (1), (Part 1 of 2) (2), (3)

Clock Network	Parameter	Symbol	C1		C2, C2L, I2, I2L		C3, I3, I3L, I3YY		C4,I4		Unit
NEIWUIK			Min	Max	Min	Max	Min	Max	Min	Max	
	Clock period jitter	t _{JIT(per)}	-50	50	-50	50	-55	55	-55	55	ps
Regional	Cycle-to-cycle period jitter	t _{JIT(cc)}	-100	100	-100	100	-110	110	-110	110	ps
	Duty cycle jitter	$t_{JIT(duty)}$	-50	50	-50	50	-82.5	82.5	-82.5	82.5	ps
	Clock period jitter	t _{JIT(per)}	-75	75	-75	75	-82.5	82.5	-82.5	82.5	ps
Global	Cycle-to-cycle period jitter	t _{JIT(cc)}	-150	150	-150	150	-165	165	-165	165	ps
	Duty cycle jitter	t _{JIT(duty)}	- 75	75	-75	75	-90	90	-90	90	ps

⁽¹⁾ This error specification is the absolute maximum and minimum error. For example, skew on three DQS delay buffers in a −2 speed grade is ±78 ps or ±39 ps.

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Duty Cycle Distortion (DCD) Specifications

Table 44 lists the worst-case DCD for Stratix V devices.

Table 44. Worst-Case DCD on Stratix V I/O Pins (1)

Symbol	C	1	C2, C2	L, I2, I2L		3, I3L, 3YY	C4	1,14	Unit	
-	Min	Max	Min	Max	Min	Max	Min	Max		
Output Duty Cycle	45	55	45	55	45	55	45	55	%	

Note to Table 44:

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POR Delay Specification

Power-on reset (POR) delay is defined as the delay between the time when all the power supplies monitored by the POR circuitry reach the minimum recommended operating voltage to the time when the nSTATUS is released high and your device is ready to begin configuration.



For more information about the POR delay, refer to the *Hot Socketing and Power-On Reset in Stratix V Devices* chapter.

Table 45 lists the fast and standard POR delay specification.

Table 45. Fast and Standard POR Delay Specification (1)

POR Delay	Minimum	Maximum
Fast	4 ms	12 ms
Standard	100 ms	300 ms

Note to Table 45:

JTAG Configuration Specifications

Table 46 lists the JTAG timing parameters and values for Stratix V devices.

Table 46. JTAG Timing Parameters and Values for Stratix V Devices

Symbol	Description	Min	Max	Unit
t _{JCP}	TCK clock period (2)	30	_	ns
t _{JCP}	TCK clock period (2)	167	_	ns
t _{JCH}	TCK clock high time (2)	14	_	ns
t _{JCL}	TCK clock low time (2)	14	_	ns
t _{JPSU (TDI)}	TDI JTAG port setup time	2	_	ns
t _{JPSU (TMS)}	TMS JTAG port setup time	3	_	ns

⁽¹⁾ The DCD numbers do not cover the core clock network.

⁽¹⁾ You can select the POR delay based on the MSEL settings as described in the MSEL Pin Settings section of the "Configuration, Design Security, and Remote System Upgrades in Stratix V Devices" chapter.

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Table 48. Minimum Configuration Time Estimation for Stratix V Devices

Variant	Member		Active Serial ⁽¹⁾		Fast Passive Parallel (2)		
	Code	Width	DCLK (MHz)	Min Config Time (s)	Width	DCLK (MHz)	Min Config Time (s)
	D3	4	100	0.344	32	100	0.043
	D4	4	100	0.534	32	100	0.067
GS		4	100	0.344	32	100	0.043
us 	D5	4	100	0.534	32	100	0.067
	D6	4	100	0.741	32	100	0.093
	D8	4	100	0.741	32	100	0.093
E	E9	4	100	0.857	32	100	0.107
	EB	4	100	0.857	32	100	0.107

Notes to Table 48:

Fast Passive Parallel Configuration Timing

This section describes the fast passive parallel (FPP) configuration timing parameters for Stratix V devices.

DCLK-to-DATA[] Ratio for FPP Configuration

FPP configuration requires a different DCLK-to-DATA[] ratio when you enable the design security, decompression, or both features. Table 49 lists the DCLK-to-DATA[] ratio for each combination.

Table 49. DCLK-to-DATA[] Ratio (1) (Part 1 of 2)

Configuration Scheme	Decompression	Design Security	DCLK-to-DATA[] Ratio
	Disabled	Disabled	1
FPP ×8	Disabled	Enabled	1
IFF X0	Enabled	Disabled	2
	Enabled	Enabled	2
	Disabled	Disabled	1
FPP ×16	Disabled	Enabled	2
	Enabled	Disabled	4
	Enabled	Enabled	4

⁽¹⁾ DCLK frequency of 100 MHz using external CLKUSR.

⁽²⁾ Max FPGA FPP bandwidth may exceed bandwidth available from some external storage or control logic.

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Table 49. DCLK-to-DATA[] Ratio (1) (Part 2 of 2)

Configuration Scheme	Decompression	Design Security	DCLK-to-DATA[] Ratio
	Disabled	Disabled	1
FPP ×32	Disabled	Enabled	4
1FF ×32	Enabled	Disabled	8
	Enabled	Enabled	8

Note to Table 49:

(1) Depending on the DCLK-to-DATA [] ratio, the host must send a DCLK frequency that is r times the data rate in bytes per second (Bps), or words per second (Wps). For example, in FPP ×16 when the DCLK-to-DATA [] ratio is 2, the DCLK frequency must be 2 times the data rate in Wps. Stratix V devices use the additional clock cycles to decrypt and decompress the configuration data.



If the DCLK-to-DATA[] ratio is greater than 1, at the end of configuration, you can only stop the DCLK (DCLK-to-DATA[] ratio -1) clock cycles after the last data is latched into the Stratix V device.

Figure 11 shows the configuration interface connections between the Stratix V device and a MAX II or MAX V device for single device configuration.

Figure 11. Single Device FPP Configuration Using an External Host



Notes to Figure 11:

- (1) Connect the resistor to a supply that provides an acceptable input signal for the Stratix V device. V_{CCPGM} must be high enough to meet the V_{IH} specification of the I/O on the device and the external host. Altera recommends powering up all configuration system I/Os with V_{CCPGM}.
- (2) You can leave the nceo pin unconnected or use it as a user I/O pin when it does not feed another device's nce pin.
- (3) The MSEL pin settings vary for different data width, configuration voltage standards, and POR delay. To connect MSEL, refer to the MSEL Pin Settings section of the "Configuration, Design Security, and Remote System Upgrades in Stratix V Devices" chapter.
- (4) If you use FPP $\times 8$, use DATA [7..0]. If you use FPP $\times 16$, use DATA [15..0].

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Table 50 lists the timing parameters for Stratix V devices for FPP configuration when the DCLK-to-DATA[] ratio is 1.

Table 50. FPP Timing Parameters for Stratix V Devices (1)

Symbol	Parameter	Minimum	Maximum	Units
t _{CF2CD}	nCONFIG low to CONF_DONE low	_	600	ns
t _{CF2ST0}	nconfig low to nstatus low	_	600	ns
t _{CFG}	nCONFIG low pulse width	2	_	μS
t _{STATUS}	nstatus low pulse width	268	1,506 ⁽²⁾	μS
t _{CF2ST1}	nCONFIG high to nSTATUS high	_	1,506 ⁽³⁾	μS
t _{CF2CK} (6)	nCONFIG high to first rising edge on DCLK	1,506	_	μS
t _{ST2CK} (6)	nSTATUS high to first rising edge of DCLK	2	_	μS
t _{DSU}	DATA[] setup time before rising edge on DCLK	5.5	_	ns
t _{DH}	DATA[] hold time after rising edge on DCLK	0	_	ns
t _{CH}	DCLK high time	$0.45 \times 1/f_{MAX}$	_	S
t _{CL}	DCLK low time	$0.45 \times 1/f_{MAX}$	_	S
t _{CLK}	DCLK period	1/f _{MAX}	_	S
f	DCLK frequency (FPP ×8/×16)	_	125	MHz
f _{MAX}	DCLK frequency (FPP ×32)	_	100	MHz
t _{CD2UM}	CONF_DONE high to user mode (4)	175	437	μS
t _{CD2CU}	GOVER DOVER high to GUVERN anabled	4 × maximum		
	CONF_DONE high to CLKUSR enabled	DCLK period	_	
t _{CD2UMC}	CONF_DONE high to user mode with CLKUSR option on	t _{CD2CU} + (8576 × CLKUSR period) ⁽⁵⁾	_	_

Notes to Table 50:

- (1) Use these timing parameters when the decompression and design security features are disabled.
- (2) This value is applicable if you do not delay configuration by extending the nCONFIG or nSTATUS low pulse width.
- (3) This value is applicable if you do not delay configuration by externally holding the nstatus low.
- (4) The minimum and maximum numbers apply only if you chose the internal oscillator as the clock source for initializing the device.
- (5) To enable the CLKUSR pin as the initialization clock source and to obtain the maximum frequency specification on these pins, refer to the Initialization section of the "Configuration, Design Security, and Remote System Upgrades in Stratix V Devices" chapter.
- (6) If nSTATUS is monitored, follow the t_{ST2CK} specification. If nSTATUS is not monitored, follow the t_{CF2CK} specification.

FPP Configuration Timing when DCLK-to-DATA [] > 1

Figure 13 shows the timing waveform for FPP configuration when using a MAX II device, MAX V device, or microprocessor as an external host. This waveform shows timing when the DCLK-to-DATA [] ratio is more than 1.

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Active Serial Configuration Timing

Table 52 lists the DCLK frequency specification in the AS configuration scheme.

Table 52. DCLK Frequency Specification in the AS Configuration Scheme (1), (2)

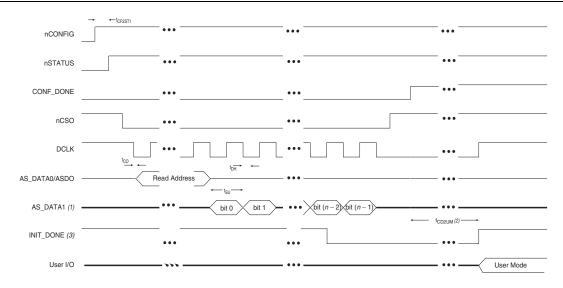
Minimum	Typical	Maximum	Unit
5.3	7.9	12.5	MHz
10.6	15.7	25.0	MHz
21.3	31.4	50.0	MHz
42.6	62.9	100.0	MHz

Notes to Table 52:

- (1) This applies to the DCLK frequency specification when using the internal oscillator as the configuration clock source.
- (2) The AS multi-device configuration scheme does not support DCLK frequency of 100 MHz.

Figure 14 shows the single-device configuration setup for an AS ×1 mode.

Figure 14. AS Configuration Timing



Notes to Figure 14:

- (1) If you are using AS ×4 mode, this signal represents the AS_DATA [3..0] and EPCQ sends in 4-bits of data for each DCLK cycle.
- (2) The initialization clock can be from internal oscillator or ${\tt CLKUSR}$ pin.
- (3) After the option bit to enable the $INIT_DONE$ pin is configured into the device, the $INIT_DONE$ goes low.

Table 53 lists the timing parameters for AS $\times 1$ and AS $\times 4$ configurations in Stratix V devices.

Table 53. AS Timing Parameters for AS \times 1 and AS \times 4 Configurations in Stratix V Devices (1), (2) (Part 1 of 2)

Symbol	Parameter	Minimum	Maximum	Units
t _{CO}	DCLK falling edge to AS_DATAO/ASDO output	_	2	ns
t _{SU}	Data setup time before falling edge on DCLK	1.5	_	ns
t _H	Data hold time after falling edge on DCLK	0	_	ns

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Table 60. Glossary (Part 3 of 4)

Letter	Subject	Definitions				
	SW (sampling window)	Timing Diagram—the period of time during which the data must be valid in order to capture it correctly. The setup and hold times determine the ideal strobe position within the sampling window, as shown: Bit Time 0.5 x TCCS RSKM Sampling Window (SW) 0.5 x TCCS				
S	Single-ended voltage referenced I/O standard	The JEDEC standard for SSTL and HSTL I/O defines both the AC and DC input signal values. The AC values indicate the voltage levels at which the receiver must meet its timing specifications. The DC values indicate the voltage levels at which the final logic state of the receiver is unambiguously defined. After the receiver input has crossed the AC value, the receiver changes to the new logic state. The new logic state is then maintained as long as the input stays beyond the DC threshold. This approach is intended to provide predictable receiver timing in the presence of input waveform ringing: Single-Ended Voltage Referenced I/O Standard VIHACO VIHACO VILLOCO V				
	t _C	High-speed receiver and transmitter input and output clock period.				
	TCCS (channel- to-channel-skew)	The timing difference between the fastest and slowest output edges, including t_{CO} variation and clock skew, across channels driven by the same PLL. The clock is included in the TCCS measurement (refer to the <i>Timing Diagram</i> figure under SW in this table).				
		High-speed I/O block—Duty cycle on the high-speed transmitter output clock.				
T	t _{DUTY}	Timing Unit Interval (TUI) The timing budget allowed for skew, propagation delays, and the data sampling window. (TUI = $1/(\text{receiver input clock frequency multiplication factor}) = t_C/w)$				
	t _{FALL}	Signal high-to-low transition time (80-20%)				
	t _{INCCJ}	Cycle-to-cycle jitter tolerance on the PLL clock input.				
	t _{OUTPJ_IO}	Period jitter on the general purpose I/O driven by a PLL.				
	t _{OUTPJ_DC}	Period jitter on the dedicated clock output driven by a PLL.				
	t _{RISE}	Signal low-to-high transition time (20-80%)				
U	_	_				

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Document Revision History

Table 61 lists the revision history for this chapter.

Table 61. Document Revision History (Part 1 of 3)

Date	Version	Changes		
June 2018	3.9	■ Added the "Stratix V Device Overshoot Duration" figure.		
		■ Added a footnote to the "High-Speed I/O Specifications for Stratix V Devices" table.		
		■ Changed the minimum value for t _{CD2UMC} in the "PS Timing Parameters for Stratix V Devices" table.		
		■ Changed the condition for 100-Ω R _D in the "OCT Without Calibration Resistance Tolerance Specifications for Stratix V Devices" table.		
April 2017	3.8	■ Changed the minimum value for t _{CD2UMC} in the "AS Timing Parameters for AS '1 and AS '4 Configurations in Stratix V Devices" table		
		■ Changed the minimum value for t _{CD2UMC} in the "FPP Timing Parameters for Stratix V Devices When the DCLK-to-DATA[] Ratio is >1" table.		
		■ Changed the minimum value for t _{CD2UMC} in the "FPP Timing Parameters for Stratix V Devices When the DCLK-to-DATA[] Ratio is >1" table.		
		■ Changed the minimum number of clock cycles value in the "Initialization Clock Source Option and the Maximum Frequency" table.		
June 2016	3.7	■ Added the V _{ID} minimum specification for LVPECL in the "Differential I/O Standard Specifications for Stratix V Devices" table		
Julie 2010		■ Added the I _{OUT} specification to the "Absolute Maximum Ratings for Stratix V Devices" table.		
December 2015	3.6	■ Added a footnote to the "High-Speed I/O Specifications for Stratix V Devices" table.		
December 2015	3.5	■ Changed the transmitter, receiver, and ATX PLL data rate specifications in the "Transceiver Specifications for Stratix V GX and GS Devices" table.		
December 2013		■ Changed the configuration .rbf sizes in the "Uncompressed .rbf Sizes for Stratix V Devices" table.		
		■ Changed the data rate specification for transceiver speed grade 3 in the following tables:		
		"Transceiver Specifications for Stratix V GX and GS Devices"		
		■ "Stratix V Standard PCS Approximate Maximum Date Rate"		
		■ "Stratix V 10G PCS Approximate Maximum Data Rate"		
July 2015	3.4	■ Changed the conditions for reference clock rise and fall time, and added a note to the "Transceiver Specifications for Stratix V GX and GS Devices" table.		
-		Added a note to the "Minimum differential eye opening at receiver serial input pins" specification in the "Transceiver Specifications for Stratix V GX and GS Devices" table.		
		■ Changed the t _{CO} maximum value in the "AS Timing Parameters for AS '1 and AS '4 Configurations in Stratix V Devices" table.		
		■ Removed the CDR ppm tolerance specification from the "Transceiver Specifications for Stratix V GX and GS Devices" table.		

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